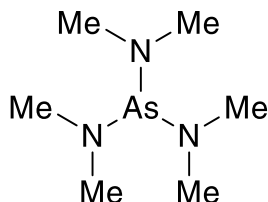


Catalog # 33-5000 Tris(dimethylamino)arsine, 99%



Thermal Behavior:

- Melting Point: -53°C
- Boiling Point: 55 °C/10 Torr

Technical Notes:

1. ALD/CVD precursor and dopant for thin arsenic containing film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
MnAs	ALD	-	10 Torr	(MeCp) ₂ Mn, H ₂	320-500°C	1
Ga _x As _y N	ALD	42°C	-	Et ₃ Ga, N ₂ H ₃ Me ₃ , H ₂	380-430°C	2, 3
GaAs	ALD AACVD	42°C Toluene Solution	- AP	Et ₃ Ga, H ₂ Me ₃ Ga	480-520°C 450°C, 500°C, 550°C	3 4
As ₂ S ₃	ALD	19°C	7.5 Torr	H ₂ S	40-50°C	5

References:

1. [J. Cryst. Growth **2007**, 298, 90.](#)
2. [J. Cryst. Growth **2009**, 311, 2821.](#)
3. [Thin Solid Films **2013**, 540, 79.](#)
4. [RSC Adv. **2015**, 5, 11812.](#)
5. [J. Vac. Sci. Technol. A, **2017**, 35, 01B114.](#)